

• General Description

This silicon carbide Power MOSFET device has been developed using ZMJ’s advanced 1st generation SiC MOSFET technology. The device features a very low $R_{DS(on)}$ over the entire temperature range combined with low capacitances and very high switching operations. It improves application performance in frequency, energy efficiency, system size and weight reduction.

• Features

- High Blocking Voltage
- High Speed Switching With Low Capacitances
- Low $R_{DS(on)}$ to Minimize Conductive Loss
- Low Gate Charge For Fast Switching
- Low Thermal Resistance
- 100% Avalanche Tested
- AEC-Q101 Qualified

• Application

- Motor Drives
- On Board Charger
- DC-DC
- Auxiliary Drives

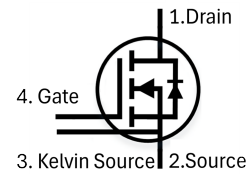
• Ordering Information:

Part NO.	ZMCA020N120C4
Marking	ZMC020N120
Packing Information	Bulk Tube
Basic Ordering Unit (pcs)	600

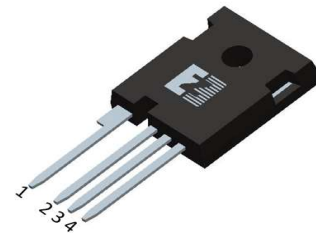
• Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		1200	V
Gate-Source Voltage	V_{GS}	Transient Voltage	-10V/25V	V
	V_{GS}	Static Voltage	-10V/24V	V
Recommended turn on gate voltage	$V_{GS(on)}$		15 to 18V	V
Recommended turn off gate voltage	$V_{GS(off)}$		-4V to 0V	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	84	A
	I_D	$T_C=75^{\circ}C$	69	A
	I_D	$T_C=100^{\circ}C$	59	A

• Product Summary



$V_{DS} = 1200V$
 $R_{DS(ON)} = 20m\Omega$
 $I_D = 84A$



TO-247-4



Pulsed Drain Current ^①	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$;	336	A
Total Power Dissipation	P_D	$T_C = 25 \text{ }^\circ\text{C}$	375	W
Total Power Dissipation	P_D	$T_A = 25 \text{ }^\circ\text{C}$	3.8	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L = 0.5\text{mH}$, $V_{GS} = 18\text{V}$, $R_g = 25\Omega$	1225	mJ
ESD Level (HBM)			Class2	

• Thermal Resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance, Junction - Case	R_{thJC}	-	-	0.4	$^\circ\text{C/W}$
Thermal Resistance, Junction-Ambient	R_{thJA} Ⓞ	-	-	40	$^\circ\text{C/W}$
Soldering Temperature (total time < 10s)	T_{sold}	-	-	260	$^\circ\text{C}$

• Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	1200	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 5\text{mA}$	2	2.9	4	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS} = 0\text{V}$, $V_{DS} = 1200\text{V}$	-	-	10	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = -10\text{V}$, $V_{DS} = 0\text{V}$	-	-	-100	nA
		$V_{GS} = 25\text{V}$, $V_{DS} = 0\text{V}$	-	-	100	nA
Static Drain-Source On Resistance	$R_{DS(on)}$	$T_J = 25 \text{ }^\circ\text{C}$, $V_{GS} = 18\text{V}$, $I_D = 60\text{A}$	-	20	26	m Ω
		$T_J = 175 \text{ }^\circ\text{C}$, $V_{GS} = 18\text{V}$, $I_D = 60\text{A}$	-	47	-	m Ω
		$T_J = 25 \text{ }^\circ\text{C}$, $V_{GS} = 15\text{V}$, $I_D = 60\text{A}$	-	26	-	m Ω
Forward Transconductance	g_{fs}	$V_{DS} = 20\text{V}$, $I_{SD} = 60\text{A}$	-	27	-	S
Diode Forward Voltage	V_{FSD}	$V_{GS} = -4\text{V}$, $I_{SD} = 60\text{A}$	-	3.8	5	V

• Dynamic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input Capacitance	C_{iss}	$f = 100\text{KHz}$, $V_{DS} = 800\text{V}$	-	4840	-	pF
Output Capacitance	C_{oss}		-	190	-	
Reverse Transfer Capacitance	C_{riss}		-	8	-	
Output Charge	Q_{oss}	$f = 100\text{KHz}$, $V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 800\text{V}$	-	266	-	nC
Coss Stored Energy	E_{oss}		-	72	-	μJ
Gate Resistance	R_g	$f = 1\text{MHz}$	-	1.9	-	Ω
Total Gate Charge	Q_g	$V_{DD} = 800\text{V}$, $I_D = 60\text{A}$, $V_{GS} = -4\text{V}/18\text{V}$	-	186	-	nC
Gate - Source Charge	Q_{gs}		-	65	-	
Gate - Drain Charge	Q_{gd}		-	76	-	

Turn-ON Delay Time	$t_{D(on)}$	$V_{GS}=-4V/18V, V_{DS}=800V,$ $R_G = 1\Omega, I_D = 60A$	-	20	-	ns
Turn-ON Rise Time	t_r		-	8	-	ns
Turn-Off Delay Time	$t_{D(off)}$		-	45	-	ns
Turn-Off Fall Time	t_f		-	20	-	ns
Turn-On Energy	E_{on}		-	465	-	uJ
Turn-Off Energy	E_{off}		-	138	-	uJ
Reverse Recovery Time	t_{rr}	$V_{DD}=800V, di_S/dt =$ $100A/us, I_S=60A$	-	21	-	ns
Reverse Recovery Peak Current	I_{rrm}		-	15	-	A
Reverse Recovery Charge	Q_{rr}		-	198	-	nC

● Characteristics Diagrams

Fig.1 Gate-Charge Characteristics

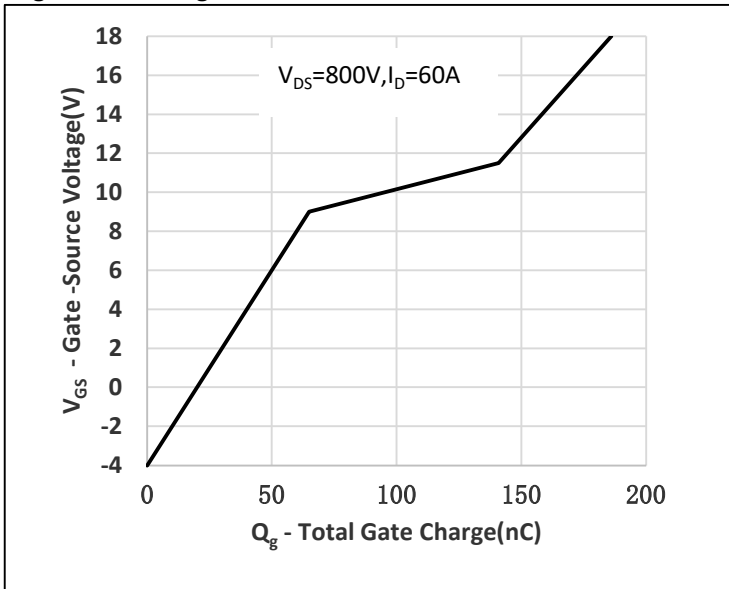


Fig.2 Capacitance Characteristics

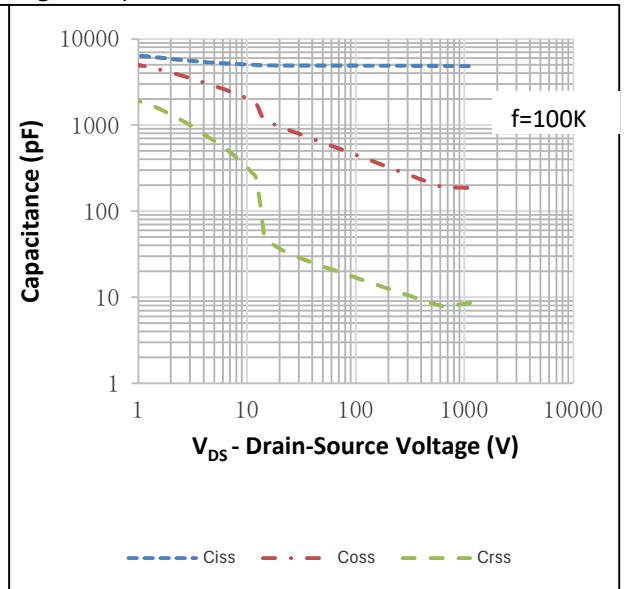


Fig.3 Power Dissipation

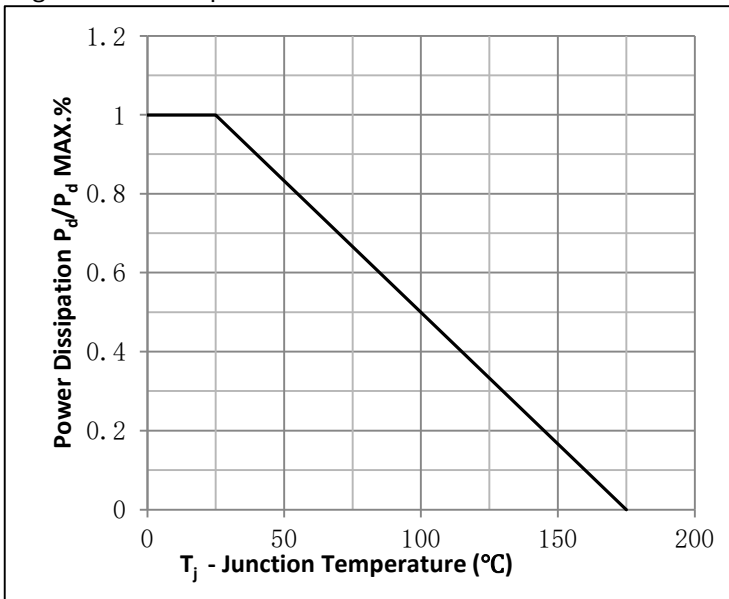


Fig.4 Typical Output Characteristics

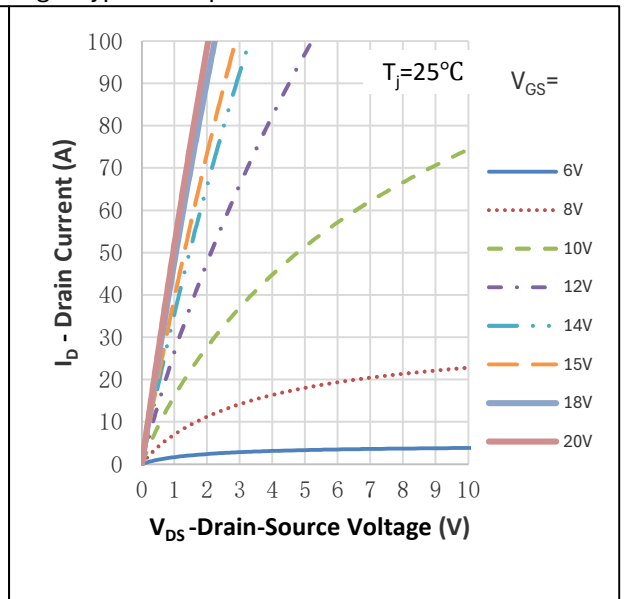


Fig.5 Threshold Voltage vs. Junction Temperature

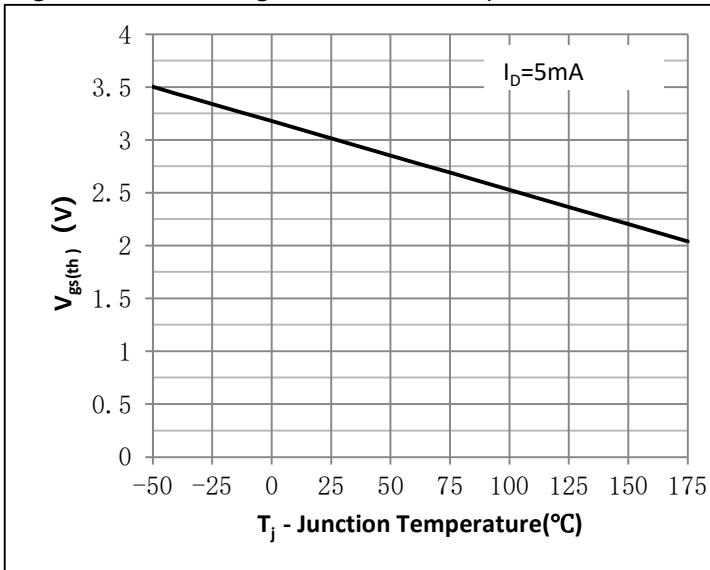


Fig.6 On-Resistance vs. Drain Current

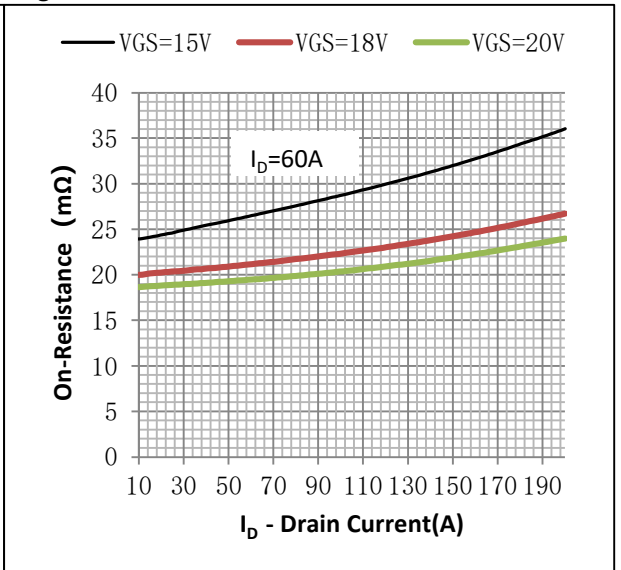


Fig.7 On-Resistance vs. Gate Source Voltage

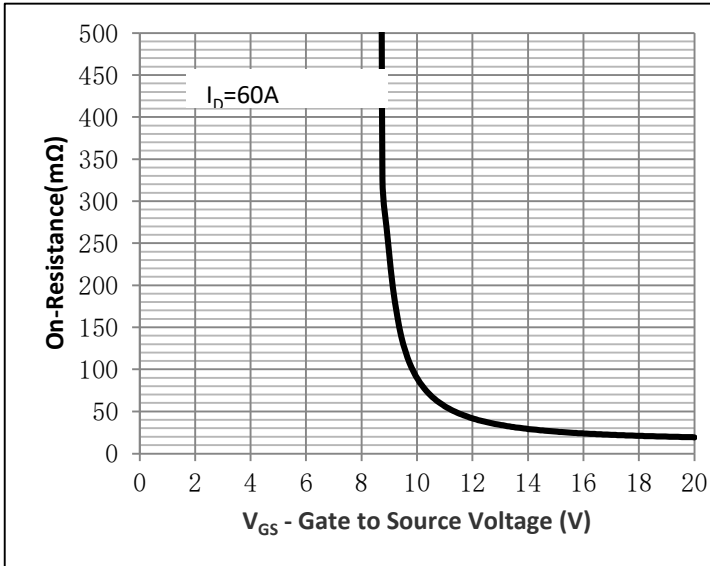


Fig.8 On-Resistance vs. Junction Temperature

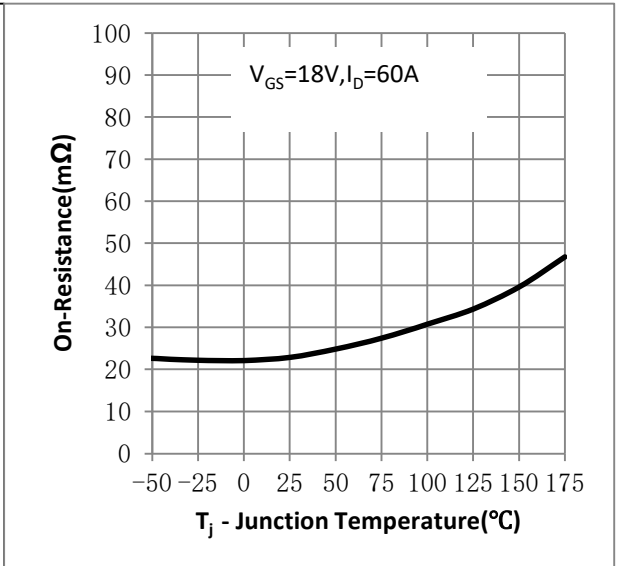


Figure 9. Diode Forward Voltage vs. Current

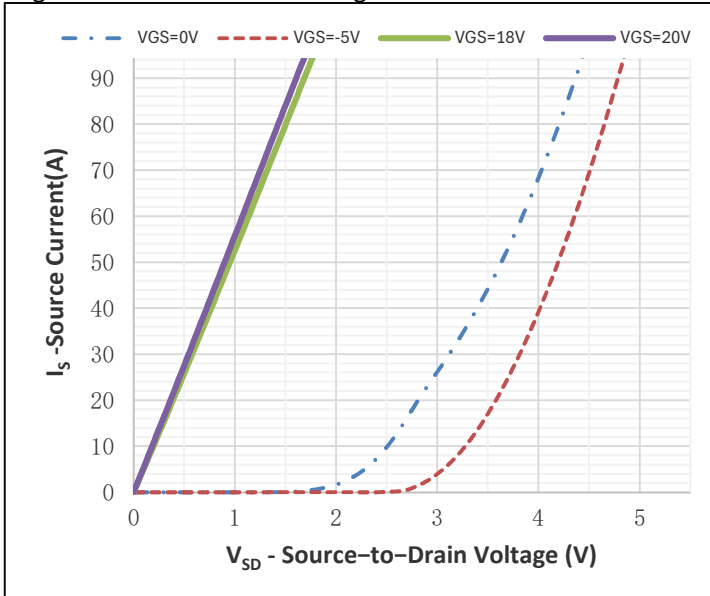


Figure 10. Transfer Characteristics

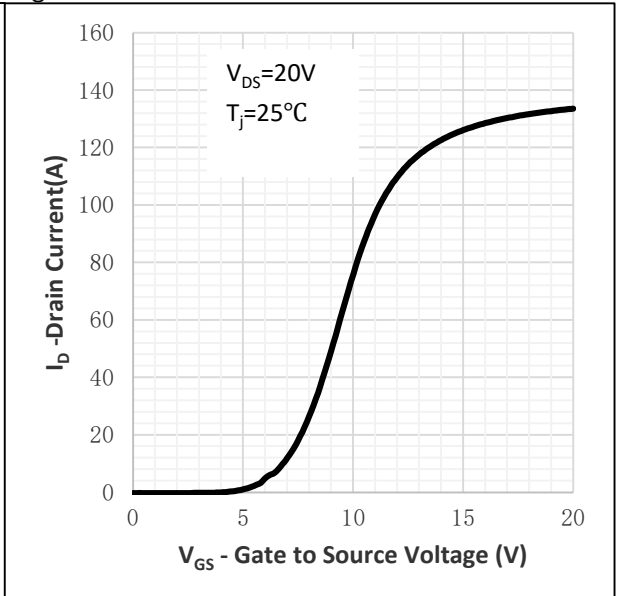


Fig.11 SOA Maximum Safe Operating Area

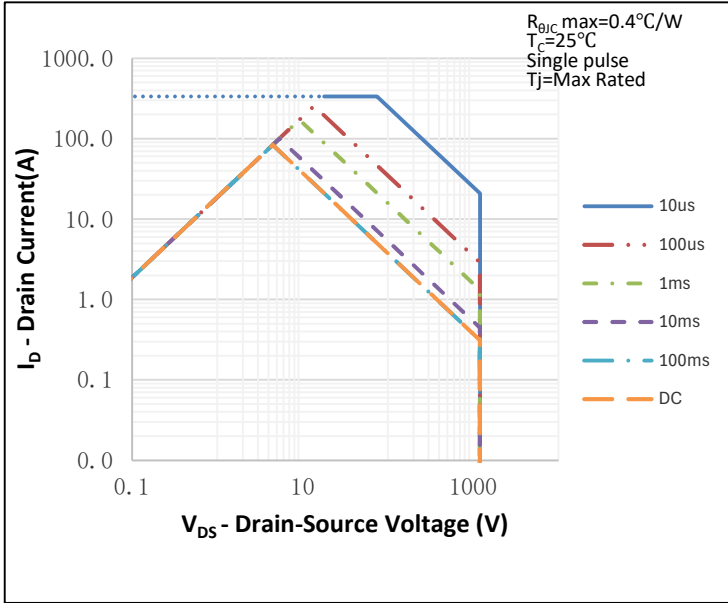


Fig.12 I_D vs. Junction Temperature

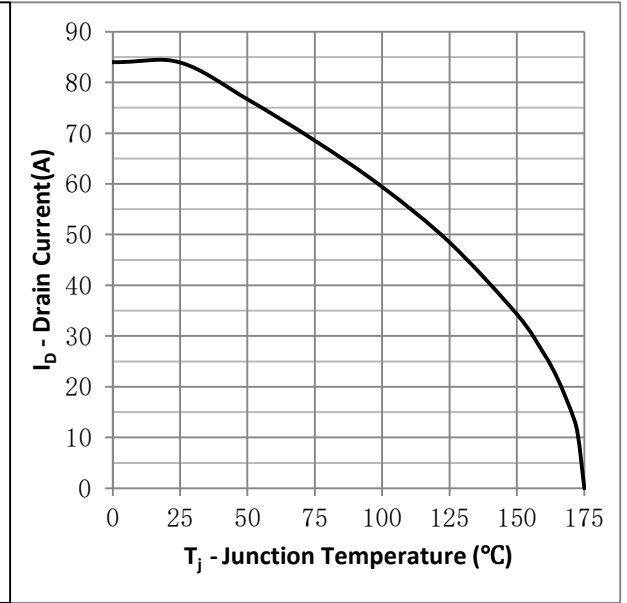


Fig.13 Output Capacitor Stored Energy

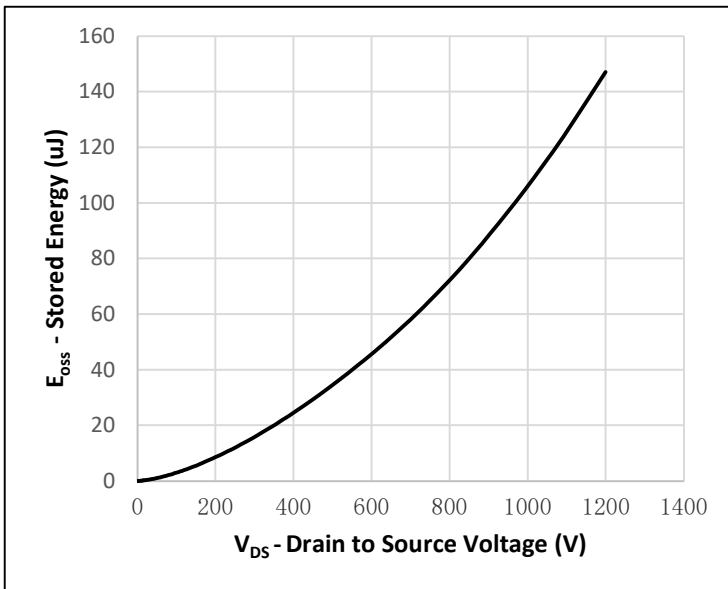
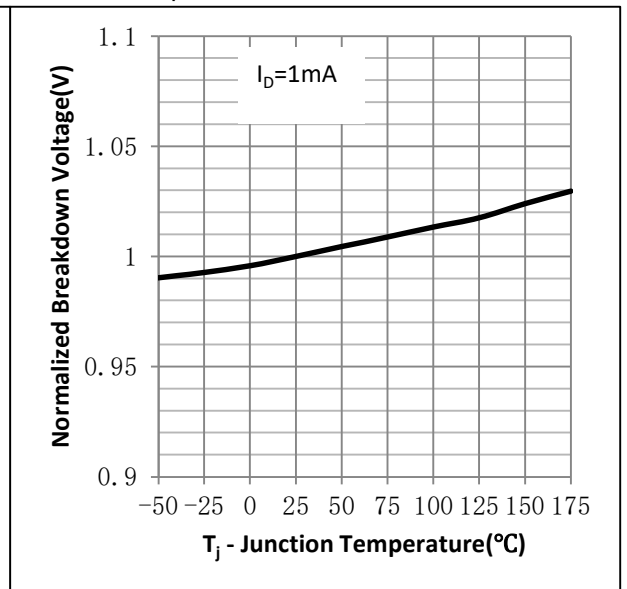
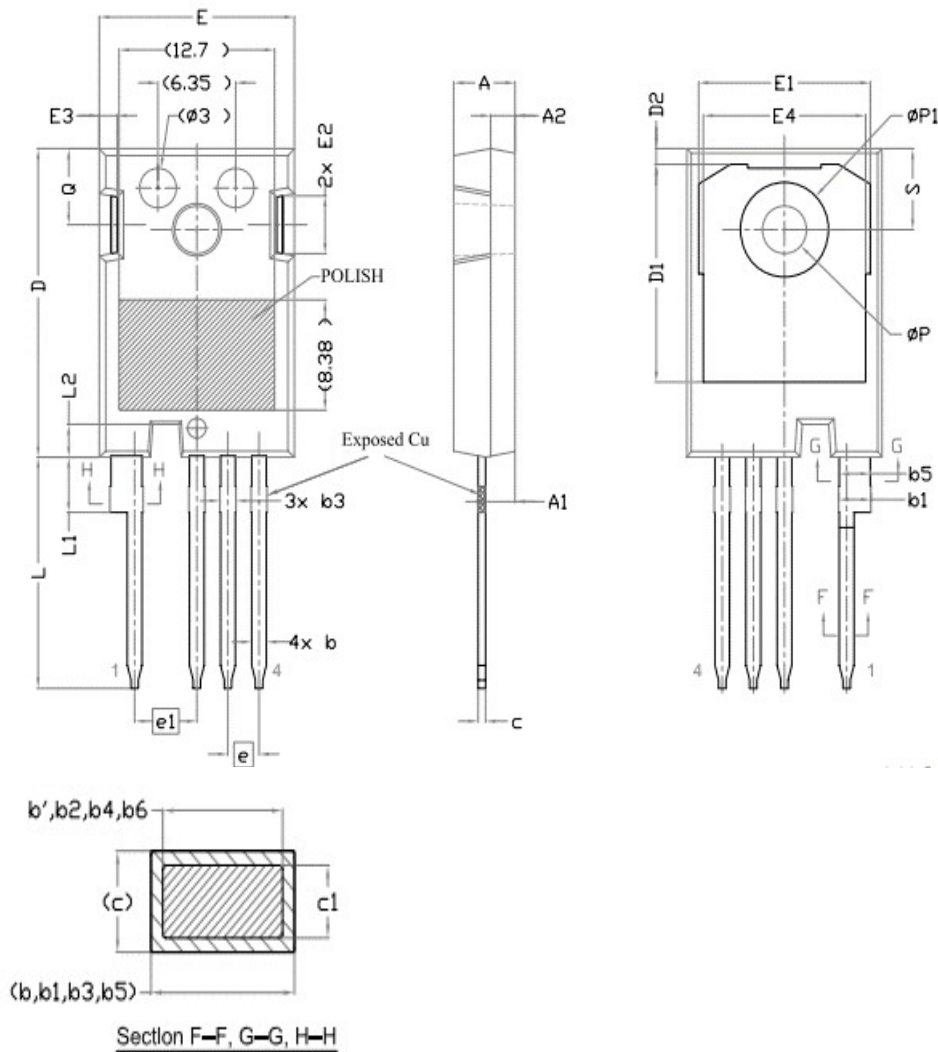


Fig.14 Normalized Breakdown Voltage vs. Junction Temperature



•TO-247-4 Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.83	5.02	5.21
A1	2.29	2.41	2.54
A2	1.91	2.00	2.16
b'	1.07	1.20	1.28
b	1.07	1.20	1.33
b1	2.39	2.67	2.94
b2	2.39	2.67	2.84
b3	1.07	1.30	1.60
b4	1.07	1.30	1.50
b5	2.39	2.53	2.69
b6	2.39	2.53	2.64
c	0.55	0.60	0.68
c1	0.55	0.60	0.65
D	23.30	23.45	23.60
D1	16.25	16.55	17.65
D2	0.95	1.19	1.25
E	15.75	15.94	16.13
E1	13.10	14.02	14.15
E2	3.68	4.40	5.10
E3	1.00	1.45	1.90
E4	12.38	13.26	13.43
e	2.54 BSC		
e1	5.08 BSC		
L	17.31	17.57	17.82
L1	3.97	4.19	4.37
L2	2.35	2.50	2.65
∅P	3.51	3.61	3.65
∅P1	7.19 REF.		
Q	5.49	5.79	6.00
S	6.04	6.17	6.30

Note:

- ① The value of $R\theta JA$ is measured with the device in a still environment with $T_A=25^{\circ}C$
- ② Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=18V$.

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Revision History:

Version	Date	Change
A	2024/6/19	New
B	2024/11/22	Update VGS maximum rating and IGSS+ test condition.